Octal D-Type Latch with 3-State Output

The MC74VHCT573A is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT573A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage—input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 7.7 \text{ ns (Typ)}$ at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 1.6 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 234 FETs or 58.5 Equivalent Gates
- Pb-Free Packages are Available*

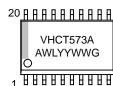


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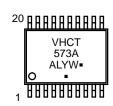
http://onsemi.com

MARKING DIAGRAMS









A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = = Pb-Free Package
(Note: Microdot may be in either location)

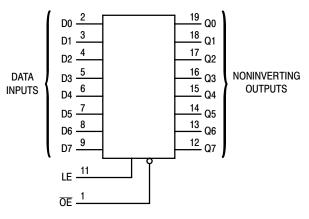
FUNCTION TABLE

	INPUTS	OUTPUT	
OE	LE	D	Q
L	Н	Н	Н
L	H	L	L
l L	L	X	No Change
l H	X	X	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





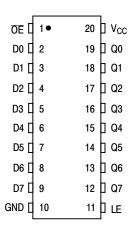


Figure 2. Pin Assignment

MAXIMUM RATINGS

Symbol	Paramete	r	Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	Outputs in 3–State High or Low State	- 0.5 to + 7.0 - 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current (V _{OUT} < 0	GND; V _{OUT} > V _{CC})	± 20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
Icc	DC Supply Current, V _{CC} and G	ND Pins	± 75	mA
P _D	Power Dissipation in Still Air,	SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage Outputs in 3–State High or Low State	0	5.5 V _{CC}	٧
T _A	Operating Temperature	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time V _{CC} =5.0V ±0.5V	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC} T _A = 25°C		°C	$T_A = -40 \text{ to } 85^{\circ}\text{C}$			
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V _{OH}	Minimum High-Level Output	$I_{OH} = -50\mu A$	4.5	4.4	4.5		4.4		V
	Voltage $V_{in} = V_{IH}$ or V_{IL}	I _{OH} = - 8mA	4.5	3.94			3.80		
V _{OL}	Maximum Low-Level Output	I _{OL} = 50μA	4.5		0.0	0.1		0.1	V
	Voltage $V_{in} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 8mA	4.5			0.36		0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
l _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μΑ
I _{CCT}	Quiescent Supply Current	Per Input: V _{IN} = 3.4V Other Input: V _{CC} or GND	5.5			1.35		1.50	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0			0.5		5.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

				•	T _A = 25	°C	T _A = - 40) to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		7.7 8.5	12.3 13.3	1.0 1.0	13.5 14.5	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, D to Q	$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.1 5.9	8.5 9.5	1.0 1.0	9.5 10.5	ns
t _{PZL} , t _{PZH}	Output Enable Time, OE to Q	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$			6.3 7.1	10.9 11.9	1.0 1.0	12.5 13.5	ns
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Q	$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C _L = 50pF		8.8	11.2	1.0	12.0	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 5.5 ± 0.5V (Note 1)	C _L = 50pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum 3–State Output Capacitance (Output in High–Impedance State)				6				pF

		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 2)	25	pF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C			
Symbol	Parameter	Тур	Max	Unit	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	1.2	1.6	V	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-1.2	-1.6	V	
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V	
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V	

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

TIMING REQUIREMENTS (Input $t_f = t_f = 3.0 \text{ns}$)

			T _A = 25°C		T _A = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _{w(h)}	Minimum Pulse Width, LE	$V_{CC} = 5.0 \pm 0.5 V$		6.5	8.5	ns
t _{su}	Minimum Setup Time, D to LE	$V_{CC} = 5.0 \pm 0.5 V$		1.5	1.5	ns
t _h	Minimum Hold Time, D to LE	$V_{CC} = 5.0 \pm 0.5 V$		3.5	3.5	ns

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT573ADW	SOIC-20WB	38 Units / Rail
MC74VHCT573ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT573ADWR2	SOIC-20WB	1000 / Tape & Reel
MC74VHCT573ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT573ADT	TSSOP-20*	75 Units / Rail
MC74VHCT573ADTG	TSSOP-20*	75 Units / Rail
MC74VHCT573ADTR2	TSSOP-20*	2500 / Tape & Reel
MC74VHCT573ADTRG	TSSOP-20*	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb–Free.

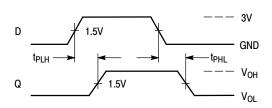


Figure 3. Switching Waveform

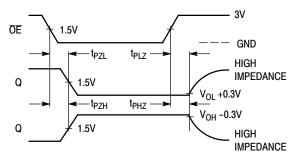


Figure 5. Switching Waveform

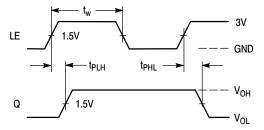


Figure 4. Switching Waveform

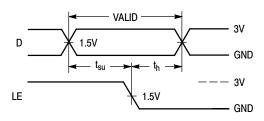
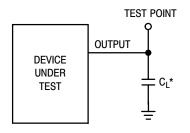
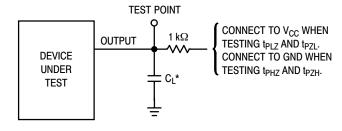


Figure 6. Switching Waveform





*Includes all probe and jig capacitance

Figure 7. Test Circuit

Figure 8. Test Circuit

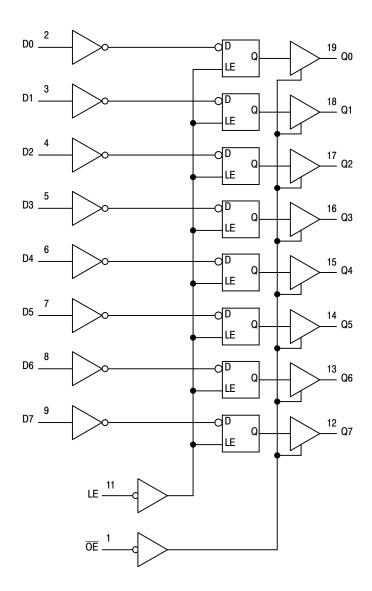
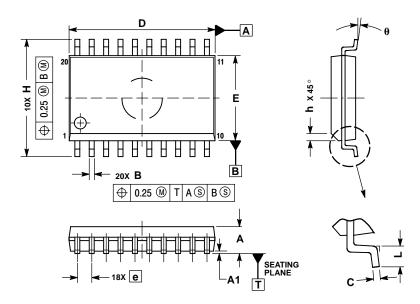


Figure 9. Expanded Logic Diagram

^{*}Includes all probe and jig capacitance

PACKAGE DIMENSIONS

SOIC-20 WB **DW SUFFIX** CASE 751D-05 **ISSUE G**

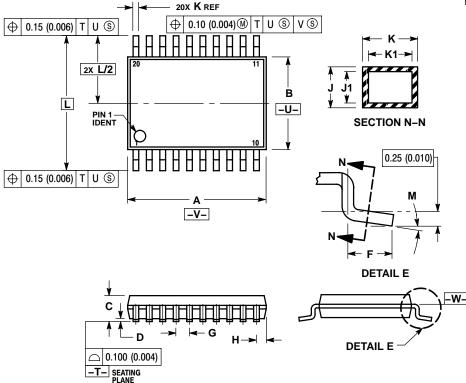


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

PACKAGE DIMENSIONS

TSSOP-20 **D5 SUFFIX** CASE 948E-02 ISSUE B



- NOTES:
 1. DIMENSIONING AND TOLERANCING
 - PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION:
 - MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS
 - SHALL NOT EXCEED 0.15 (0.006) PER SIDE DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER
 - 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - TERMINAL NUMBERS ARE SHOWN
 - FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
٦	6.40		0.252 BSC		
M	0°	8°	0°	8°	

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